Abstract

RELAXATION OF A STRAINED MATERIAL LAYER WITH APPLICATION OF A STIFFENER

The invention relates to a method of fabricating a layer of at least partially relaxed material (5,5a,5b) for electronics, optoelectronics or photovoltaics comprising the supply of a structure (10) including a layer of strained material (3 ,3a,3b), situated between a reflow layer (2 ,2a,2b), and a stiffener layer (4 ,4a,4b) the application of a heat treatment that brings the reflow layer (2 ,2a,2b) to a temperature equal to or greater than the glass transition temperature of said reflow layer (2 ,2a,2b) characterized in that the method comprises the progressive reduction in the thickness of the stiffener layer (4 ,4a,4b) during application of said heat treatment.

The invention also relates to a method of fabricating semiconductor devices comprising the supply of a layer of material that is at least partially relaxed (5, 5a, 5b) obtained following the previous method, characterized in that the method also comprises the formation of at least one active layer (6, 6a, 6b) on the at least partially relaxed material layer (5, 5a, 5b), in particular active layers (6, 6a, 6b) of laser components, photovoltaic components or electroluminescent diodes.

(Figure 1)